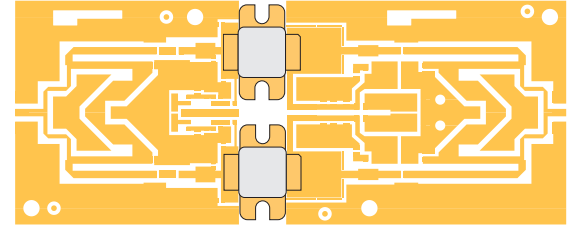


S-Band GaN/SiC, RF Power Amplifier Pallet

2.5-3.1 GHz | 3 kW typ | 60% Efficiency typ | 12 dB Gain typ | 100 V | 100µs Pulse Length, 1% Duty Cycle

IGNP2531M2600 is a high power GaN-on-SiC RF power amplifier pallet that has been designed to suit the unique needs of S-Band Directed Energy systems. It operates over the full 2.5 - 3.1 GHz frequency range. Under 100µs, 1% duty cycle pulse conditions it typically supplies 3 kW of peak output power, with typically >12 dB of gain and 60% efficiency. It operates from a 100 V supply voltage.



FEATURES

- GaN on SiC HEMT Technology
- Output Power >2600W
- Fully matched to 50Ω
- High Efficiency
- 100% RF Tested Under 100µs, 1% duty cycle pulse conditions

APPLICATIONS

- S-Band Directed Energy systems
- S-Band Radar Systems

Table 1. RF Electrical Characteristics (Case temperature = 30 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gain	G	10	12	14	dB	P _{OUT} = 2600W f = 2.5, 2.7, 2.9, 3.1 GHz 100µs pulse length, 1% duty cycle V _{DS} = 100V, I _{DS} = 200 mA
Drain Efficiency	η	55	60	65	%	
Pulse Droop	D	0	-0.3	-0.4	dB	
Load Mismatch Stability	VSWR-S	3:1				
Input Return Loss	IRL		10		dB	

Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.

Table 2. Absolute Maximum Ratings (Not Simultaneous)

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	V_{DS}	400	V	25 °C
DC Gate-Source Voltage	V_{GS}	-8 to +1	V	25 °C
DC Drain Current	I_D	60	A	25 °C
DC Gate Current	I_G	10	mA	25 °C
RF Input Power	P_{RFIN}	300	W	25 °C
Operating Channel Temperature	T_{CH}	-55 to +225	°C	
Storage Temperature	T_{STG}	-55 to +150	°C	
Soldering Temperature	T_{SOLDER}	260 for 60s	°C	

Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 3. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Typ	Max	Units	Test Conditions
Gate Pinch-Off Voltage	V_p	-5.0			V	$V_{DS} = 100V, I_{DS} = 1mA$
Quiescent Gate Voltage	V_q		-4		V	$V_{DS} = 100V, I_{DS} = 200mA$

Table 4. Thermal Resistance (Case temperature = 85 °C unless otherwise stated)

Parameter	Symbol	Typ	Units	Test Conditions
Peak Thermal Resistance, Channel to Case	R_{TH}	0.09	°C/W	$P_{DISS} = 1733W$ 100µs pulse length 1% duty cycle $V_{DS} = 100V$

TYPICAL PERFORMANCE

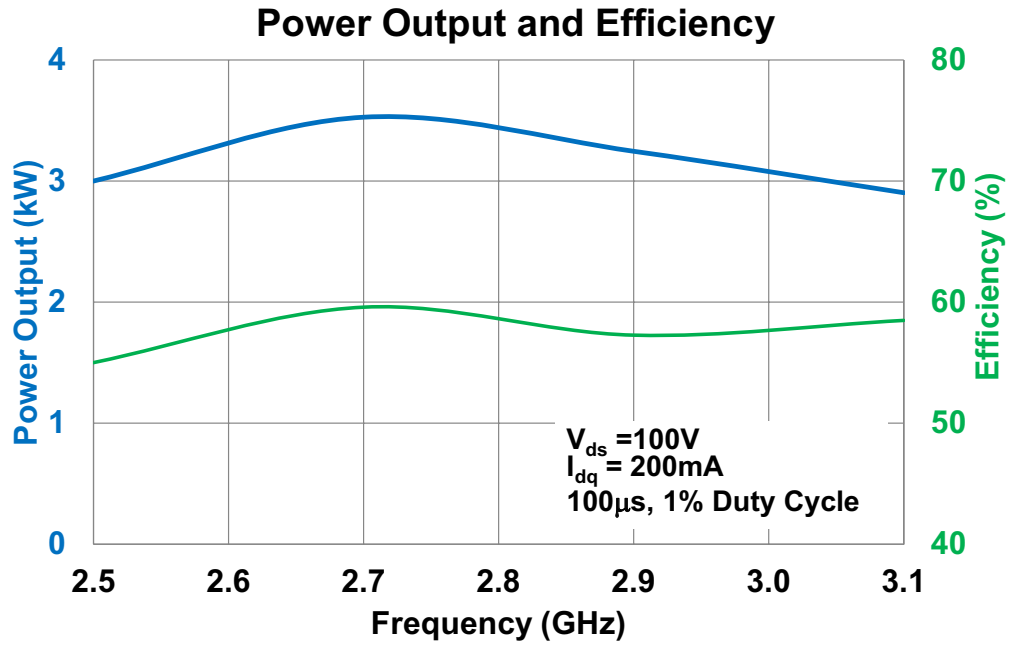
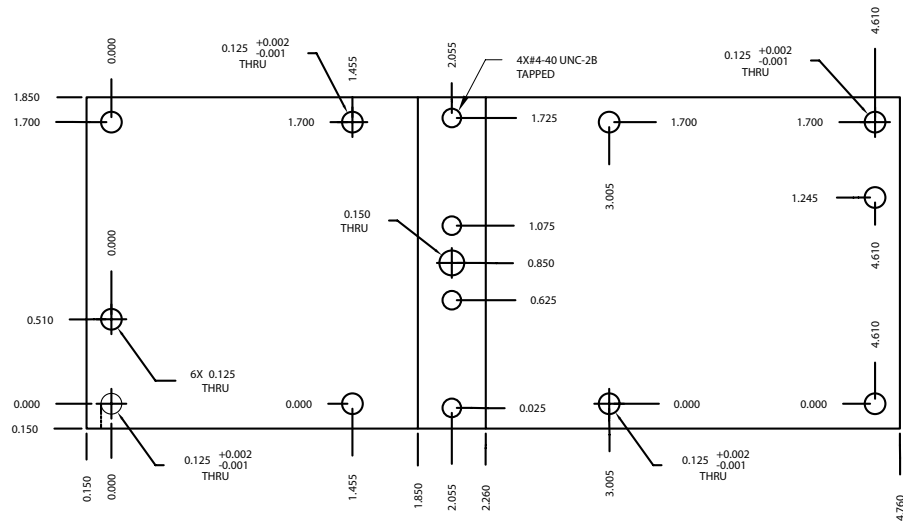
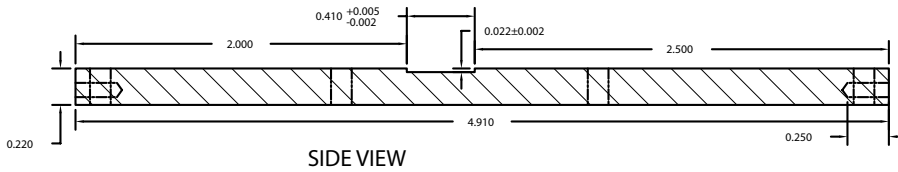


Figure 1.

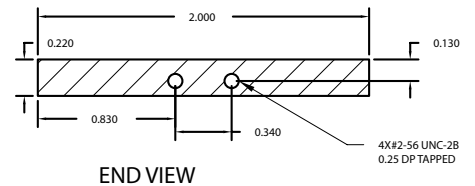
DIMENSIONS



TOP VIEW



SIDE VIEW



END VIEW

ESD & MSL Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C101F
Moisture Sensitivity Level (MSL)	Unlimited Shelf Life	IPC/JEDEC J-STD-020

REACH Compliance

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

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DEFINITIONS:

DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications.

MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.